

IN THE SPECIFICATION

Please replace the paragraph at page 4, beginning at line 19 and ending at line 27 with the following:

BRIEF SUMMARY OF THE INVENTION

A semiconductor memory device according to an aspect of the present invention, comprises:

a semiconductor substrate;
a flat-plate-shaped cavity made in the semiconductor substrate; and
an element isolating region formed in the surface of the semiconductor substrate and located at the sides of the cavity, the cavity being wider than an element region provided on the cavity.

Please replace the paragraph at page 5, beginning at line 1 and ending at line 13 with the following:

A method of fabricating a semiconductor device according to another aspect of the present invention comprises:

making flat-plate-shaped cavities partly in a semiconductor substrate;
forming an insulating film in the surface of the semiconductor substrate between adjacent ones of the cavities in such a manner that a part of the insulating film is exposed to ~~the sides of~~

the cavities so as to electrically separate element regions provided ~~at the top of~~ on the adjacent cavities from each other each cavity being wider than each element region; and
forming semiconductor elements on the element regions.